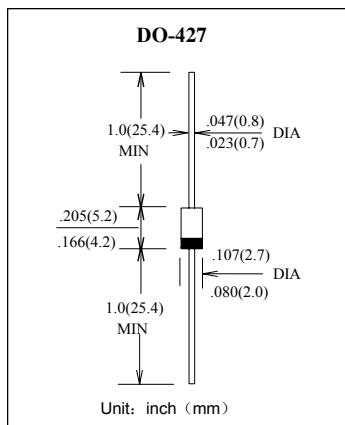




DB6

## 双向触发二极管 SILICON BIDIRECTIONAL DIAC



### Features

- Low reverse leakage
- High forward surge capability
- High temperature soldering guaranteed:  
 $2i \epsilon$   
250°C/10 seconds, 0.375" (9.5mm) lead length,
- 5 lbs. (2.3kg) tension

### Mechanical Data

- Terminals: Plated axial leads
- Polarity: Color band denotes cathode end
- Mounting Position: Any

### ABSOLUTE RATINGS ( LIMITING VALUES )

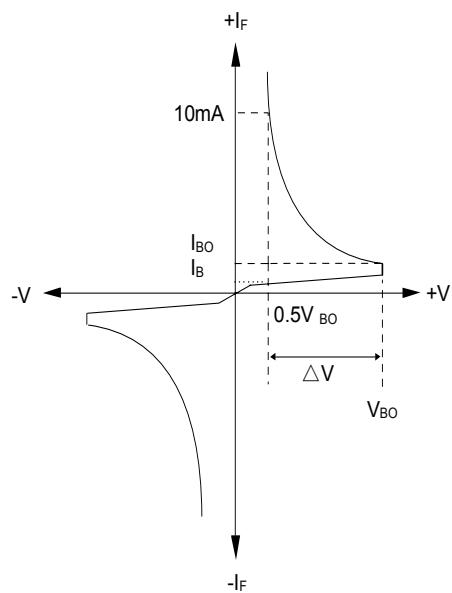
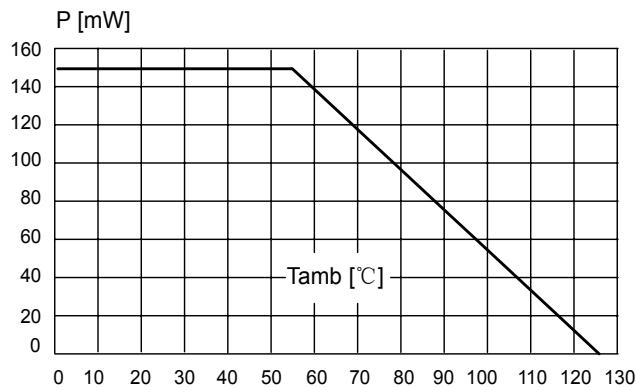
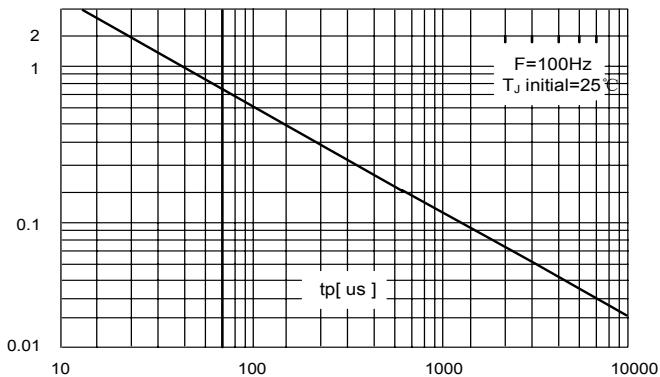
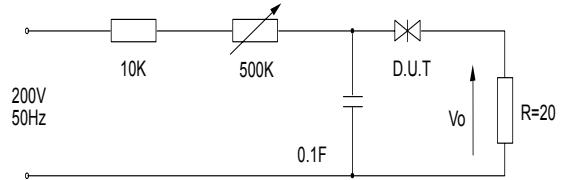
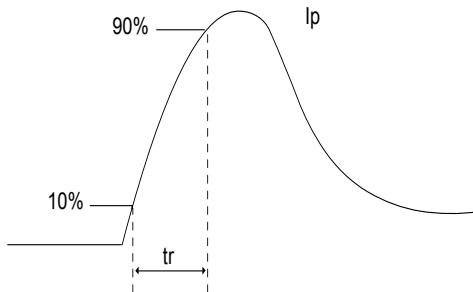
Symbols	Parameters	Value		Units
		DB6		
$P_c$	Power Dissipation on Printed Circuit [ L=10mm ]	$T_A=50^\circ\text{C}$	150	mW
$I_{TRM}$	Repetitive Peak on-state Current	$t_p=10\mu\text{s}$ $F=100\text{Hz}$	2.0	A
$T_{STG}/T_J$	Storage and Operating Junction Temperature		-40 to +125 / -40 to 110	°C

### ELECTRICAL CHARACTERISTICS

Symbols	Parameters	Test Conditions	Value		Units
			DB6		
$V_{BO}$	Breakover Voltage [Note 2 ]	C=22nF [Note 2 ] See Diagram 1	Min	56	V
			Typ	60	
			Max	70	
$ +V _{BO}$ $  -V _{BO}$	Breakover Voltage Symmetry	C=22nF [Note 2 ] See Diagram 1	Max	$\pm 5$	V
$I \pm \Delta V_I$	Dynamic Breakover Voltage [Note 1 ]	$\Delta I=[ I_{BO} \text{ to } IF=10\text{mA} ]$ See Diagram 1	Min	10	V
$V_o$	Output Voltage [Note 1 ]	See Diagram 2	Min	5	V
$I_{BO}$	Breakover Current [Note 1 ]	C=22nF [Note 2 ]	Max	100	uA
$tr$	Rise Time [Note 1 ]	See Diagram 3	Typ	1.5	uS
$I_B$	Leakage Current [Note 1 ]	$V_{BBO}=0.5\text{V max}$ See Diagram 1	Max	10	uA

Notes:1.Electrical characteristics applicable in both forward and reverse directions.

2.Connected in parallel with the devices.

**DIAGRAM 1:** Current-voltage characteristics

**FIG.1-Power dissipation versus ambient temperature ( maximum values )**

**FIG.3-Peck pulse current versus pluse duration ( maximum values )**

**DIAGRAM 2: Test circuit for output voltage**

**DIAGRAM 3: Test circuit see diagram 2 adjust R for Ip =0.5A**

**FIG.2-Relative variation of VBO versus junction temperature ( typical values )**
